

Features

- $V_{CE0} = 40V$
- $I_C = 200mA$
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- **Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Ultra Small Package**

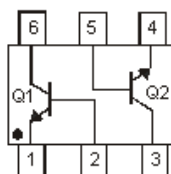
Mechanical Data

- Case: SOT-963
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe.
Solderable per MIL-STD-202, Method 208
- Weight: 0.0027 grams (approximate)

SOT-963



Top View



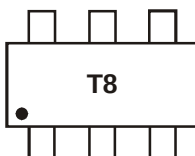
Device Schematic

Ordering Information

Device	Packaging	Shipping
DST3904DJ-7	SOT-963	10,000/Tape & Reel

Notes: 1. No purposefully added lead. Halogen and Antimony Free.
2. Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>

Marking Information



T8 = Product Type Marking Code

Maximum Ratings

@T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 3)	I _C	200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 3)	R _{θJA}	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 3. Device mounted on FR-4 PCB with minimum recommended pad layout.

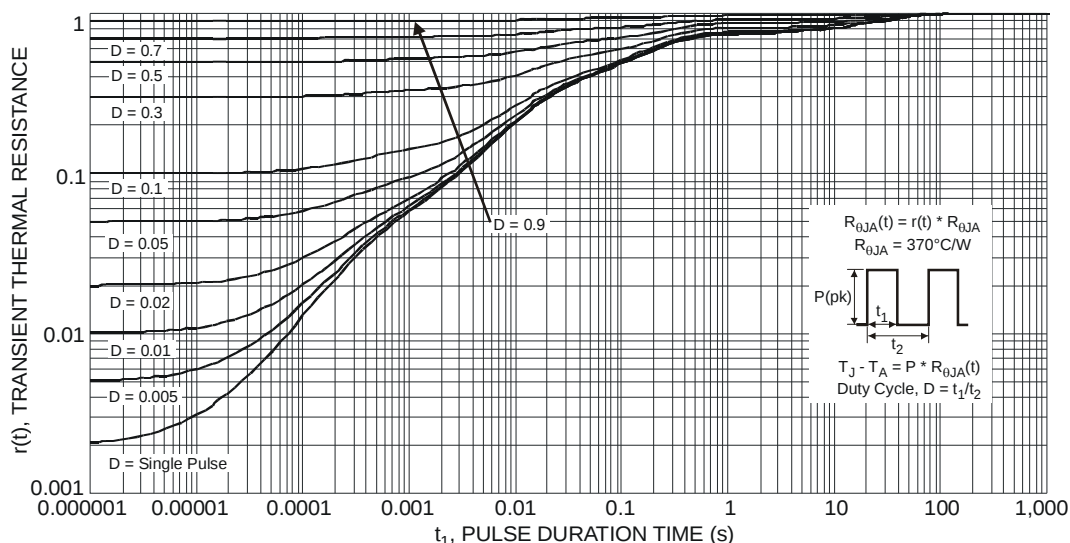


Fig. 1 Transient Thermal Response

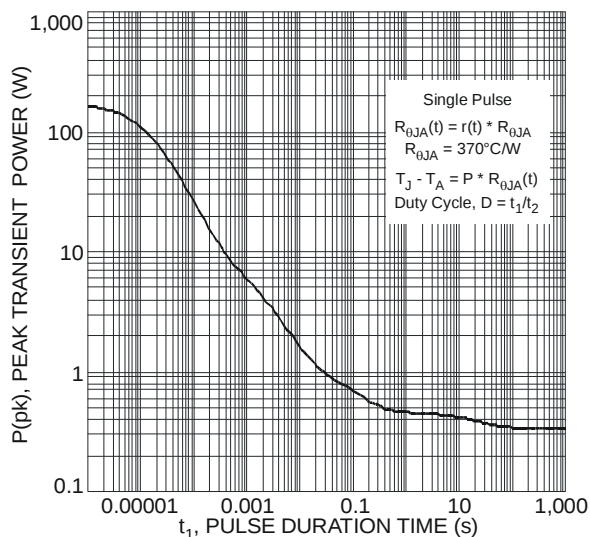


Fig. 2 Single Pulse Maximum Power Dissipation

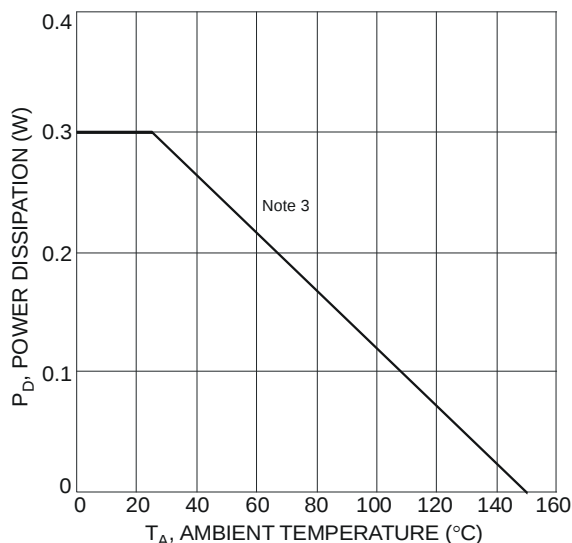
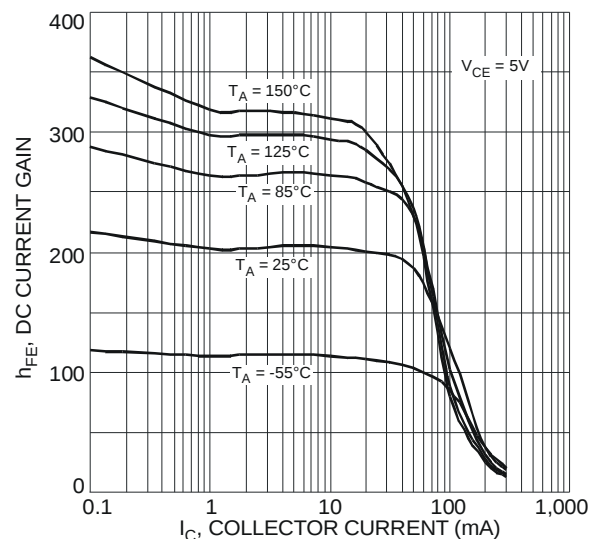
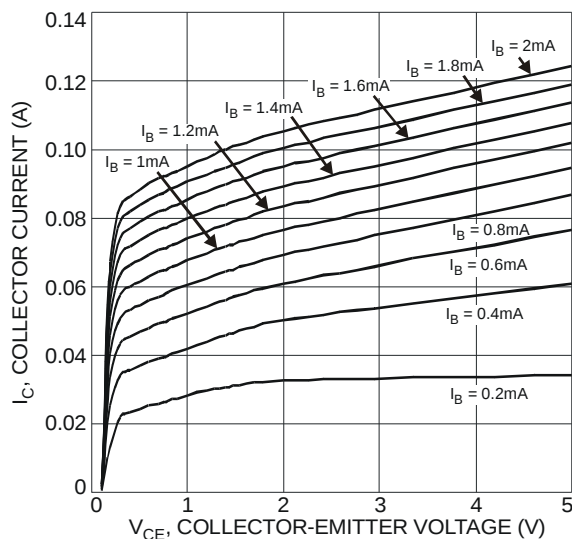


Fig. 3 Power Dissipation vs. Ambient Temperature

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 4)	V _{(BR)CEO}	40	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
Base Cutoff Current	I _{BL}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	40	—	—	I _C = 100μA, V _{CE} = 1.0V
		70	—		I _C = 1.0mA, V _{CE} = 1.0V
		100	300		I _C = 10mA, V _{CE} = 1.0V
		60	—		I _C = 50mA, V _{CE} = 1.0V
		30	—		I _C = 100mA, V _{CE} = 1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.20 0.30	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65 —	0.85 0.95	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.0	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	8.5	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1.0	10	kΩ	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.5	8.0	× 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	100	400	—	
Output Admittance	h _{oe}	1.0	40	μS	V _{CE} = 20V, I _C = 10mA, f = 100MHz
Current Gain-Bandwidth Product	f _T	300	—	MHz	
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = 3.0V, I _C = 10mA, V _{BE(off)} = - 0.5V, I _{B1} = 1.0mA
Rise Time	t _r	—	35	ns	
Storage Time	t _s	—	200	ns	V _{CC} = 3.0V, I _C = 10mA, I _{B1} = I _{B2} = 1.0mA
Fall Time	t _f	—	50	ns	

Notes: 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%



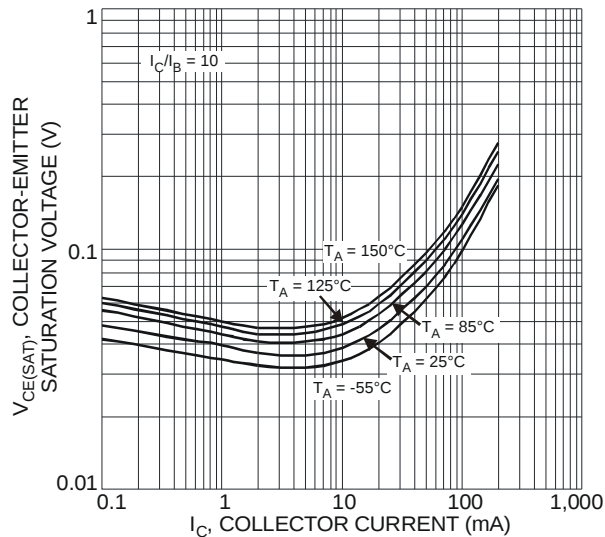


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

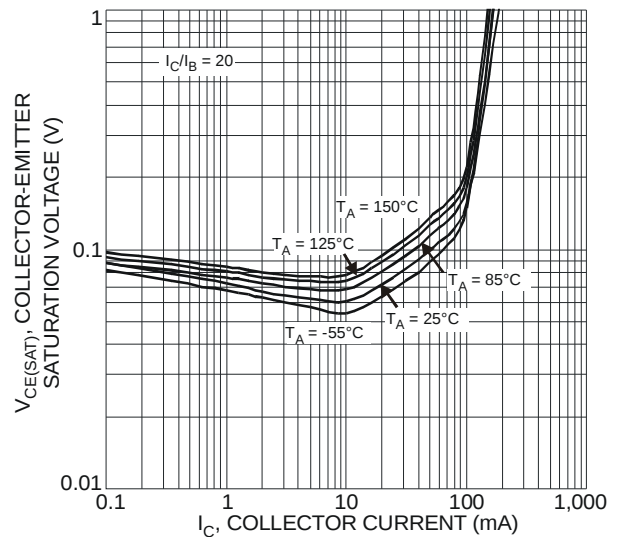


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

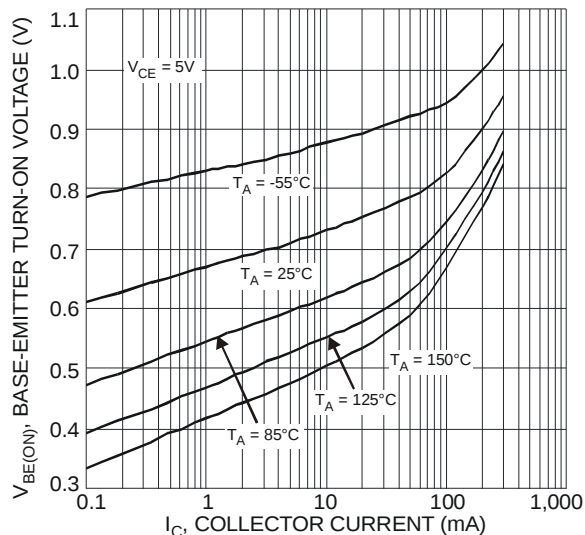


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

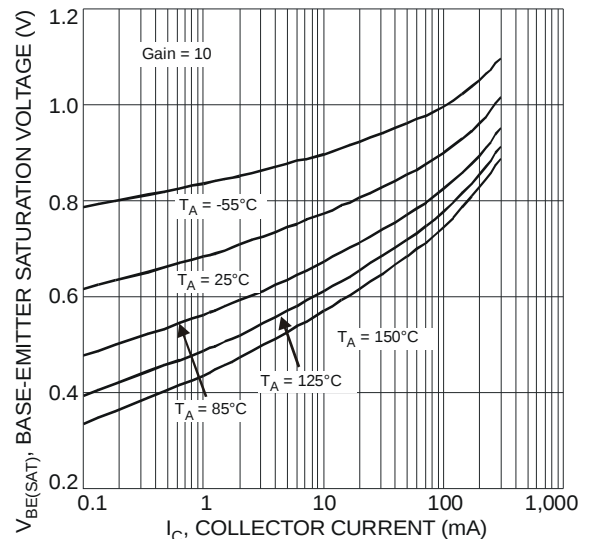


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

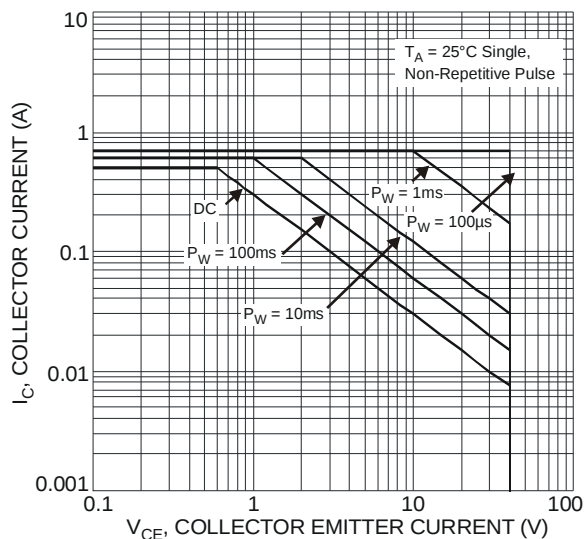
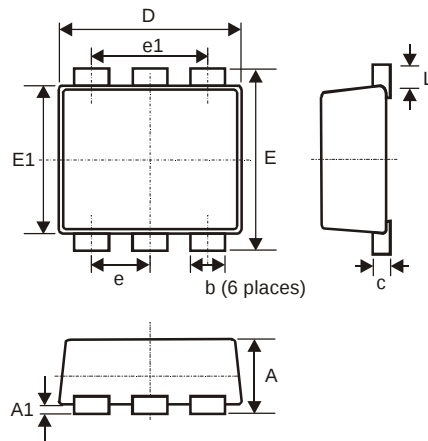


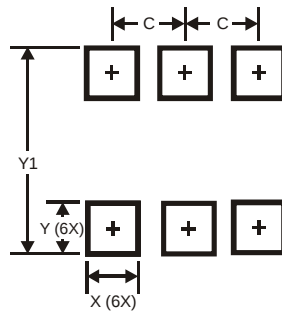
Fig. 10 Safe Operation Area (NPN)

Package Outline Dimensions



SOT-963			
Dim	Min	Max	Typ
A	0.40	0.50	0.45
A1	0	0.05	-
C	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
L	0.05	0.15	0.10
b	0.10	0.20	0.15
e	0.35 Typ		
e1	0.70 Typ		
All Dimensions in mm			

Suggest Pad Layout



Dimensions	Value (in mm)
C	0.350
X	0.200
Y	0.200
Y1	1.100

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